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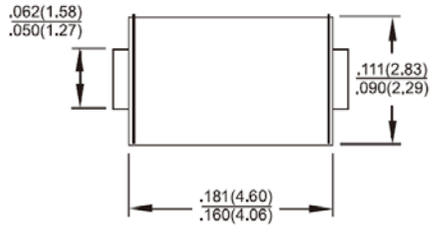
TAIWAN SEMICONDUCTOR

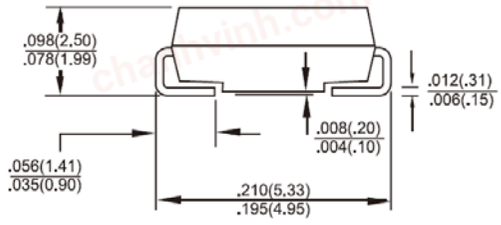
HS1A - HS1M

1.0AMP High Efficient Surface Mount Rectifiers

SMA/DO-214AC







Features

- ✧ Glass passivated junction chip.
- ✧ For surface mounted application
- ✧ Low forward voltage drop
- ✧ Low profile package
- ✧ Built-in stain relief, ideal for automatic placement
- ✧ Fast switching for high efficiency
- ✧ High temperature soldering: 260℃/10 seconds at terminals
- ✧ Plastic material used carries Underwriters Laboratory Classification 94V-0
- ✧ Green compound with suffix "G" on packing code & prefix "G" on datecode

Mechanical Data

- ✧ Cases: Molded plastic
- ✧ Terminal: Pure tin plated, lead free
- ✧ Polarity: Indicated by cathode band
- ✧ Packing: 12mm tape per EIA STD RS-481
- ✧ Weight: 0.064 grams

Dimensions in inches and (millimeters)

Marking Diagram



HS1X = Specific Device Code
G = Green Compound
Y = Year
M = Work Month

Maximum Ratings and Electrical Characteristics

Rating at 25 ℃ ambient temperature unless otherwise specified.
Single phase, half wave, 60 Hz, resistive or inductive load.
For capacitive load, derate current by 20%

Type Number	Symbol	HS 1A	HS 1B	HS 1D	HS 1F	HS 1G	HS 1J	HS 1K	HS 1M	Units
Maximum Recurrent Peak Reverse Voltage	V_{RRM}	50	100	200	300	400	600	800	1000	V
Maximum RMS Voltage	V_{RMS}	35	70	140	210	280	420	560	700	V
Maximum DC Blocking Voltage	V_{DC}	50	100	200	300	400	600	800	1000	V
Maximum Average Forward Rectified Current See Fig. 1	$I_{F(AV)}$	1								A
Peak Forward Surge Current, 8.3 ms Single Half Sine-wave Superimposed on Rated Load (JEDEC method)	I_{FSM}	30								A
Maximum Instantaneous Forward Voltage (Note 1) @ 1 A	V_F	1.0				1.3	1.7			V
Maximum DC Reverse @ T_A=25 ℃	I_R	5								uA
Current at Rated DC @ T_A=100 ℃		50								
Blocking Voltage @ T_A=125 ℃		150								
Maximum Reverse Recovery Time (Note 2)	Trr	50					75			nS
Typical Junction Capacitance (Note 3)	Cj	20					15			pF
Typical Thermal Resistance	$R_{\theta JA}$	70								$^oC/W$
Operating Temperature Range	T_J	- 55 to + 150								^oC
Storage Temperature Range	T_{STG}	- 55 to + 150								^oC

Note 1: Pulse Test with PW=300 usec, 1% Duty Cycle

Note 2: Reverse Recovery Test Conditions: I_F=0.5A, I_R=1.0A, I_{RR}=0.25A

Note 3: Measured at 1 MHz and Applied Reverse Voltage of 4.0Volts.

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RATINGS AND CHARACTERISTIC CURVES (HS1A THRU HS1M)

FIG.1- MAXIMUM AVERAGE FORWARD CURRENT DERATING

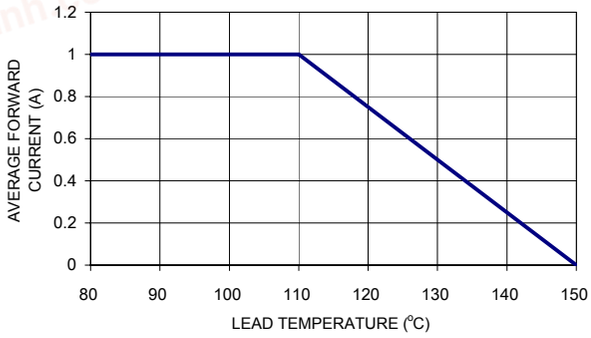


FIG. 2- TYPICAL REVERSE CHARACTERISTICS

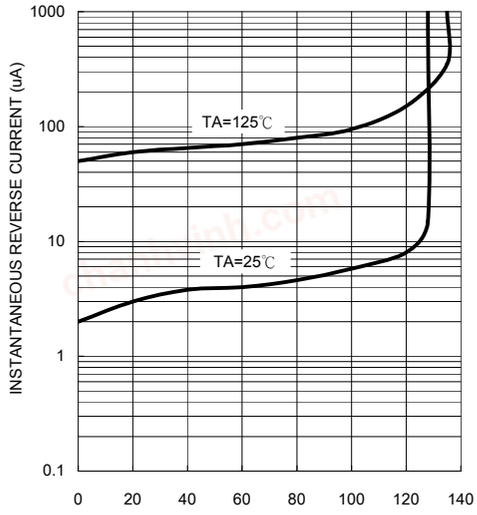


FIG. 3- MAXIMUM NON-REPETITIVE FORWARD SURGE CURRENT

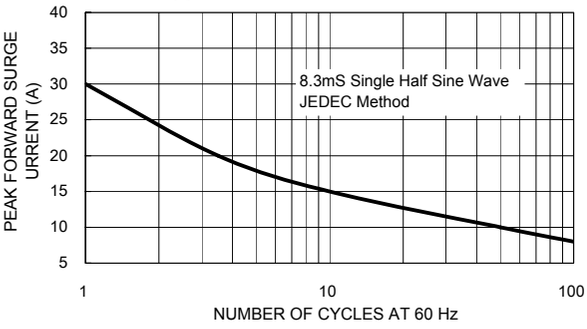


FIG. 5- TYPICAL INSTANTANEOUS FORWARD CHARACTERISRICS

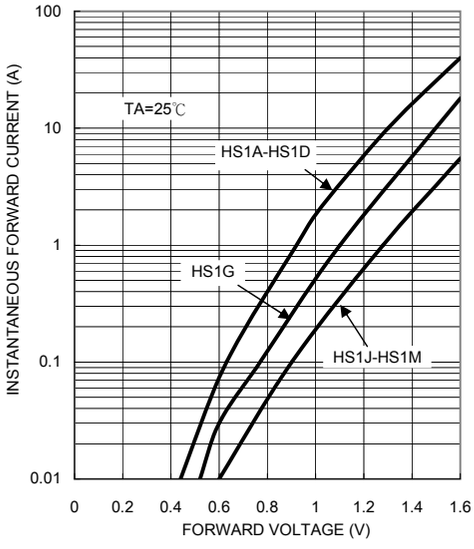


FIG. 4- TYPICAL JUNCTION CAPACITANCE

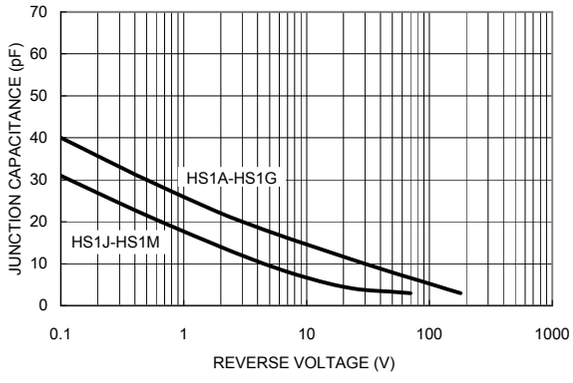


FIG.6- REVERSE RECOVERY TIME CHARACTERISTIC AND TEST CIRCUIT DIAGRAM

